

Claims 12 to 23 (canceled)

Claim 24 (withdrawn) The transistor of claim 9 wherein said first source/drain region is a source region, said second source/drain region is a drain region and wherein said first  $V_T$  is higher than said second  $V_T$ .

Claim 25 (previously added) The transistor of claim 10 wherein said first source/drain region is a source region and said second source/drain region is a drain region.

Claim 26 (withdrawn) The transistor or claim 11 wherein said first source/drain region is a source region and said second source/drain region is a drain region.

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#### REMARKS

Claim 10 has been amended, and claims 9, 11, 24 and 26 have been withdrawn from consideration. Accordingly, claims 10 and 25 are still active in this application.

Claim 10 was rejected under 35 U.S.C. 102(b) as being anticipated by Sasaki (U.S. 4,371,955 B1). The rejection is respectfully traversed.

Claim 10 requires, among other features, a channel region between the source/drain regions in the substrate having a relatively low  $V_T$  central region between the source/drain regions and relatively high  $V_T$  regions adjacent to the source/drain regions, the channel region having an implanted one of a positive or negative  $V_T$  dopant intermediate the source/drain regions and having an implanted one of a negative or positive  $V_T$  dopant adjacent the source/drain regions, the opposite of the dopant in the channel region. This claim refers to the third embodiment as discussed on page 3 of the specification. No such features are taught or suggested by Sasaki either alone or in the total combination as claimed.

Claim 25 depends from claim 10 and therefore defines patentably over Sasaki for at least the reasons set forth as to claim 10.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,



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